

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) An electronic device comprising:  
a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:
  - a gate electrode formed over the substrate;
  - a gate insulating film formed over the gate electrode;
  - a substantially intrinsic semiconductor layer formed over the gate insulating film;
  - an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;
  - at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;
  - an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and
  - a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.
  
2. (Currently Amended) An electronic device comprising:  
a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:
  - a gate electrode formed over the substrate;
  - a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

3. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

4. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

5. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

6. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

7. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

8. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

9. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic

semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

10. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

11. (Currently Amended) An electronic device comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, wherein the insulating film is in contact with an edge of the n-type semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

12. (Original) An electronic device according to any one of claims 1-11, wherein the substrate comprises one selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite, and polyimide.

13. (Original) An electronic device according to any one of claims 1-11, wherein the gate insulating film comprises silicon oxide or silicon nitride.

14. (Original) An electronic device according to any one of claims 1-11, wherein the substantially intrinsic semiconductor layer comprises amorphous silicon or microcrystalline silicon.

15. (Original) An electronic device according to any one of claims 1-11, wherein the at least one of the source and the drain electrodes comprises aluminum.

16. (Original) An electronic device according to any one of claims 1-11, wherein the insulating film comprising the resinous material comprises polyimide.

17. (Original) An electronic device according to any one of claims 1-11, wherein the pixel electrode comprises ITO.

18. (Currently Amended) A computer comprising:  
a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:  
a gate electrode formed over the substrate;  
a gate insulating film formed over the gate electrode;  
a substantially intrinsic semiconductor layer formed over the gate insulating film;  
an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;  
at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;  
an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and  
a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

19. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

20. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

21. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain electrodes electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

22. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

- a gate electrode formed over the substrate;

- a gate insulating film formed over the gate electrode;

- a substantially intrinsic semiconductor layer formed over the gate insulating film;

- an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

- at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

- an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

- a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

23. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

- a gate electrode formed over the substrate;

- a gate insulating film formed over the gate electrode;

- a substantially intrinsic semiconductor layer formed over the gate insulating film;

- an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

24. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

25. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer, wherein an edge of the at least one of the source and the drain electrodes is aligned with an edge of the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

26. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with an edge of the n-type semiconductor layer; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain ~~electrodes~~, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain ~~electrodes~~ is not formed over the n-type semiconductor layer.

27. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes, and wherein a contact portion between the pixel electrode and the at least one of the source and the drain electrodes is not formed over the n-type semiconductor layer.

28. (Currently Amended) A computer comprising:

a panel having a thin film transistor formed over a substrate, the thin film transistor comprising:

a gate electrode formed over the substrate;

a gate insulating film formed over the gate electrode;

a substantially intrinsic semiconductor layer formed over the gate insulating film;

an n-type semiconductor layer formed over the substantially intrinsic semiconductor layer;

at least one of a source and a drain ~~electrodes~~ electrode formed over the n-type semiconductor layer;

an insulating film comprising a resinous material formed over the thin film transistor, wherein the insulating film is not in contact with the substantially intrinsic semiconductor layer, wherein the insulating film is in contact with an edge of the n-type semiconductor layer, and wherein the insulating film is in contact with the gate insulating film; and

a pixel electrode formed over the insulating film, wherein the pixel electrode is in contact with the at least one of the source and the drain electrodes.

29. (Original) A computer according to any one of claims 18-28, wherein the substrate comprises one selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite, and polyimide.

30. (Original) A computer according to any one of claims 18-28, wherein the gate insulating film comprises silicon oxide or silicon nitride.

31. (Original) A computer according to any one of claims 18-28, wherein the substantially intrinsic semiconductor layer comprises amorphous silicon or microcrystalline silicon.

32. (Original) A computer according to any one of claims 18-28, wherein the at least one of the source and the drain electrodes comprises aluminum.

33. (Original) A computer according to any one of claims 18-28, wherein the insulating film comprising the resinous material comprises polyimide.

34. (Original) A computer according to any one of claims 18-28, wherein the pixel electrode comprises ITO.

35. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates;  
a layer comprising a resinous material covering the thin film transistor; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

36. (New) A display device comprising:  
a pair of flexible substrates facing each other;  
a thin film transistor formed over one of the pair of flexible substrates;  
a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

37. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates;  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

38. (New) A display device comprising:  
a pair of flexible substrates facing each other;  
a thin film transistor formed over one of the pair of flexible substrates;  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

39. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates;  
a layer comprising a resinous material covering the thin film transistor; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

40. (New) A display device comprising:  
a pair of flexible substrates facing each other;  
a thin film transistor formed over one of the pair of flexible substrates;  
a layer comprising a resinous material covering the thin film transistor; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of flexible substrates.

41. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates;  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

42. (New) A display device comprising:  
a pair of flexible substrates facing each other;  
a thin film transistor formed over one of the pair of flexible substrates;  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of flexible substrates.

43. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising amorphous silicon;  
a layer comprising a resinous material covering the thin film transistor; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

44. (New) A display device comprising:  
a pair of flexible substrates facing each other;  
a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising amorphous silicon;  
a layer comprising a resinous material covering the thin film transistor; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

45. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising amorphous silicon;  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

46. (New) A display device comprising:

a pair of flexible substrates facing each other;

a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising amorphous silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

47. (New) A display device comprising:

a pair of filmy substrates facing each other;

a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

48. (New) A display device comprising:

a pair of flexible substrates facing each other;

a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

49. (New) A display device comprising:

a pair of filmy substrates facing each other;

a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

50. (New) A display device comprising:

a pair of flexible substrates facing each other;

a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a silicon oxide film covering the thin film transistor formed, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

51. (New) A display device comprising:

a pair of filmy substrates facing each other;

a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

52. (New) A display device comprising:

a pair of flexible substrates facing each other;

a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

53. (New) A display device comprising:

a pair of filmy substrates facing each other;

a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

54. (New) A display device comprising:

a pair of flexible substrates facing each other;

a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

55. (New) A display device comprising:

a pair of filmy substrates facing each other;

a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

56. (New) A display device comprising:  
a pair of flexible substrates facing each other;  
a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;  
a layer comprising a resinous material covering the thin film transistor; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

57. (New) A display device comprising:  
a pair of filmy substrates facing each other;  
a thin film transistor formed over one of the pair of filmy substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and  
a pixel electrode formed over the layer, and electrically connected to the thin film transistor,  
wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

58. (New) A display device comprising:  
a pair of flexible substrates facing each other;

a thin film transistor formed over one of the pair of flexible substrates, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor,

wherein a resinous layer is provided on a surface of one of the pair of filmy substrates.

59. (New) A display device according to any one of claims 55-58, wherein the laser light comprises at least one selected from the group consisting of KrF excimer laser light and XeCl laser light.

60. (New) A display device according to any one of claims 39-58, wherein the resinous layer comprises an acrylic resin.

61. (New) A display device according to any one of claims 39-58, wherein the resinous layer comprises at least one selected from the group consisting of methyl esters of acrylic acid, ethyl esters of acrylic acid, butyl esters of acrylic acid, and 2-ethylhexyl esters of acrylic acid.

62. (New) A display device according to any one of claims 35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57, wherein the filmy substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

63. (New) A display device according to any one of claims 35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57, wherein the filmy substrate comprises a plastic substrate.

64. (New) A display device according to any one of claims 36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56 and 58, wherein the flexible substrate comprises a plastic substrate.

65. (New) A display device according to any one of claims 36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56 and 58, wherein the flexible substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

66. (New) A display device according to any one of claims 35-58, wherein the thin film transistor comprises a coplanar thin-film transistor.

67. (New) A display device according to any one of claims 35-58, wherein the thin film transistor comprises an inverted-staggered thin-film transistor.